

FORM PTO-1449 (SUBSTITUTE)		Attorney Docket No.: GR99P3456 Appl. No.	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Applicant HARALD KUHN ET AL.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))		Filing Date January 7, 2002 Group Art Unit	
JC992 U.S. PRO 10/04/2002 01/07/02			

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
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## FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
<i>MAA</i>	J ✓	32 30 727 A1	2/23/84	Germany			
<i>MAA</i>	K ✓	32 30 727 C2	2/23/84	Germany			
<i>MAA</i>	L ✓	0 389 533 B1	10/3/90	Europe			
<i>MAA</i>	M ✓	09 142 995 A	6/3/97	Japan			
<i>MAA</i>	N ✓	10 182 296 A	7/7/98	Japan			

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>MAA</i>	✓	Yoo, W. et al.: "Bulk Crystal Growth of 6H-SiC on Polytype-Controlled Substrates Through Vapor Phase and Characterization", Elsevier Science Publishers B.V., 1991, pp. 733-739; <i>no month</i>
<i>MAA</i>	✓	Takahashi, J. et al.: "Influence of the Seed Face Polarity on the Sublimation Growth of $\alpha$ -SiC", Jpn. J. Appl. Phys., Vol. 34, Part 1, No. 9A, September 1995, pp. 4694-4698; <i>no month</i>

EXAMINER <i>Harald Kuhn</i>	DATE CONSIDERED <i>10/29/03</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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<i>MAA</i>	J ✓	11 060 390	3/2/99	Japan			
	K						
	L						
	M						
	N						

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>MAA</i>	Jayatirtha, H. et al.: "Improvement in the Growth Rate of Cubic Silicon Carbide Bulk Single Crystals grown by the sublimation Method", Elsevier Science B.V., 1997, pp. 662-668; <i>~no note~</i>
<i>MAA</i>	Ohtani, N. et al.: "Development of Large Single-Crystal SiC Substrates", Scripta Technica, 1998, pp. 8-17; <i>~no note~</i>

EXAMINER	<i>Matthew J. Anderson</i>	DATE CONSIDERED
		10/29/03

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